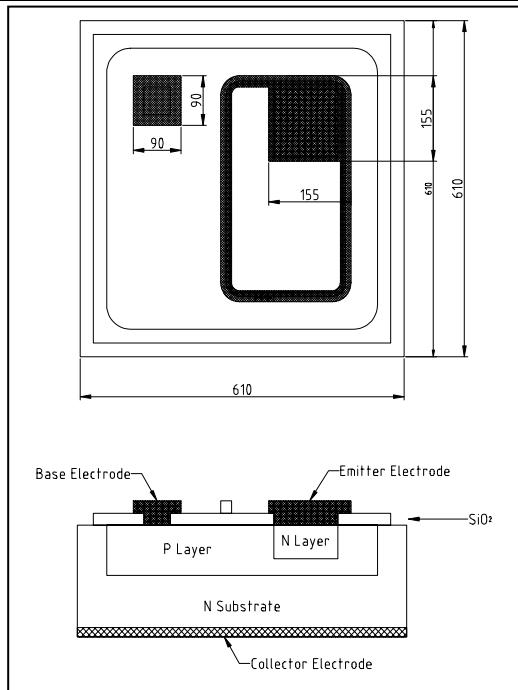


OPB0606

Silicon Photo Transistor

1. Structure

- 1.1 Chip Size : 0.61mm X 0.61mm
- 1.2 Chip thickness : 280±20um
- 1.3 Metallization : Top - Al, Bottom - Au
- 1.4 Passivation : Silicon Nitride
- 1.5 Bonding Pad Size
 - Emitter : 155um X 155um
 - Base : 90um X 90um



2. Guaranteed Probed Electrical Characteristics

(Ta=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
C-E Leakage Current	I_{CEO}			100	nA	$V_{CE}=10V$
Spectrum Sensitivity	λ	450		1100	nm	
Peak Sensing Wavelength	λ_p		880		nm	
C-E Voltage	BV_{CEO}	30			V	$I_{CE}=500\mu A$
C-B Voltage	BV_{CBO}	40			V	$I_{CB}=50\mu A$
E-B Voltage	BV_{EBO}	5			V	$I_{EB}=50\mu A$
E-C Voltage	BV_{ECO}	4			V	$I_{EC}=50\mu A$
C-E Saturation Voltage	V_{CES}			300	mV	$I_C=5mA, I_B=1mA$
Rise/Fall Time	tr/tf	15/15(Typ)			us	$V_{CE}=5V, I_C=1mA, R_L=1000\Omega$
DC Current Gain	h_{FE}	1,000		2,200	-	$V_{CE}=10V, c=1mA$

3. Hfe Bin Grade

Bin Grade	MIN	MAX
A	1,000	1,500
B	1,200	1,800
C	1,500	2,200

4. Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector Voltage	V_{ECO}	4	V

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